Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a TO263 (D2PAK) surface mountable plastic package intended for use in applications applications requiring good bidirectional blocking voltage and high surge current capability and high junction temperature capability ($T_{\text{i}(\text{max})} = 150 \, ^{\circ}\text{C}$)

2. Features and benefits

- High junction operating temperature capability (T_{i(max)} = 150 °C)
- · High bidirectional blocking voltage capability
- · Very high current surge capability
- · High thermal cycling performance
- · Planar passivated for voltage ruggedness and reliability

3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- · Inrush protection
- Motor control
- Voltage regulation

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
V_{DRM}	repetitive peak off-state voltage			600		V	
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 132 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3		30			А
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; Fig. 4; Fig. 5		360 396			А
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms					Α
T _j	junction temperature			150			°C
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$		5	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>		-	-	40	mA
V _T	on-state voltage	I _T = 30 A; T _j = 25 °C; <u>Fig. 10</u>		1.50		V	
Dynamic	characteristics						
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		500		V/µs	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	Α	anode		A K G
3	G	gate		sym037
mb	А	mounting base; connected to anode	1 3	

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
TYN30B-600TF	TO263	TYN30B-600TFJ	Reel	800	TO263d	17-Mar-2023

7. Marking

Table 4. Marking codes

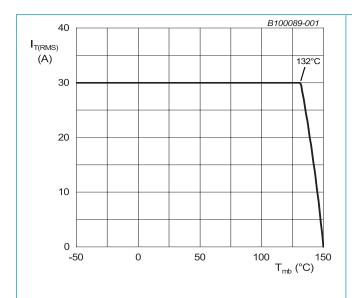
Type number	Marking codes
TYN30B-600TF	TYN30B 600TF

8. Limiting values

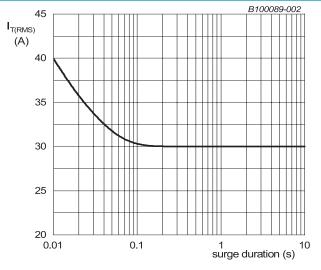
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

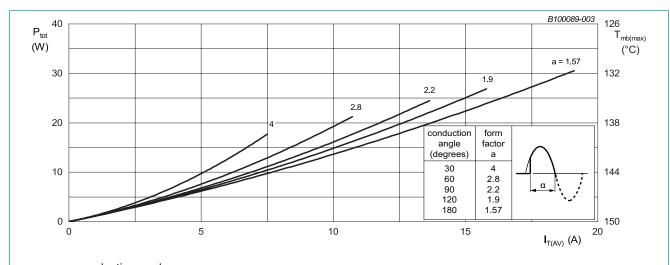
Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DRM}	repetitive peak off-state voltage			600	V
V_{RRM}	repetitive peak reverse voltage			600	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 132 °C;		19	А
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 132 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3		30	А
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; Fig. 4; Fig. 5		360	А
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms		396	Α
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse		648	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 20 mA		150	A/µs
I _{GM}	peak gate current			5	А
V_{GM}	peak gate voltage			5	V
V_{GRM}	peak reverse gate voltage			7	V
P_GM	peak gate power			20	W
$P_{G(AV)}$	average gate power	over any 20 ms period		1	W
T _{stg}	storage temperature			-40 to 150	°C
T _j	junction temperature			150	°C







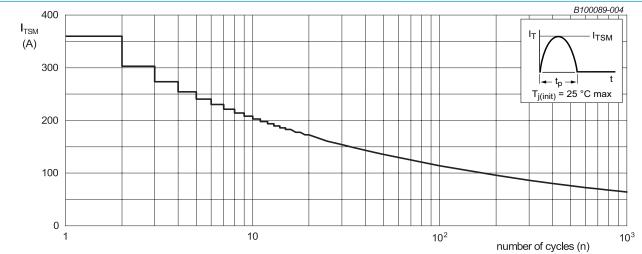
f = 50 Hz; T_{mb} = 132 °C Fig. 2. RMS on-state current as a function of surge duration; maximum values



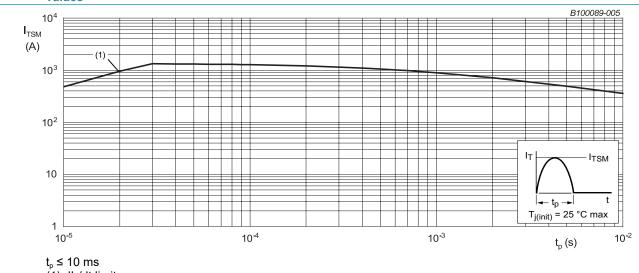
α = conduction angle

a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz
 Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



(1) dl_⊤/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	Fig. 6		-	-	0.60	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W

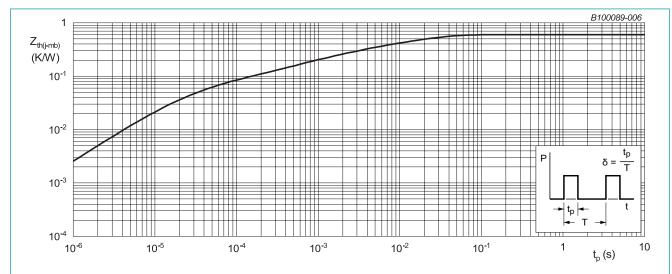


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$		5	-	10	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$		-	-	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>		-	-	40	mA
V _T	on-state voltage	I _T = 30 A; T _j = 25 °C; <u>Fig. 10</u>		-	-	1.50	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	8.0	1.0	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C		0.25	0.45	-	V
I _D	off-state current	V _D = 600 V; T _j = 25 °C		-	-	10	μA
		V _D = 600 V; T _j = 150 °C		-	-	2	mA
I _R	reverse current	V _D = 600 V; T _j = 25 °C		-	-	10	μA
		V _D = 600 V; T _j = 150 °C		-	-	2	mA
Dynamic	characteristics					1	1
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		500	-	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 30 \text{ A}; V_D = 600 \text{ V}; I_G = 100 \text{ mA};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}; T_j = 25 ^{\circ}\text{C}$		-	2	-	μs
t _q	commutated turn-off time	I_{TM} = 2 A; t_p = 50 µs; dV/dt = 5 V/µs; dI/dt = 30 A/µs; T_i = 25 °C		-	-	12	μs

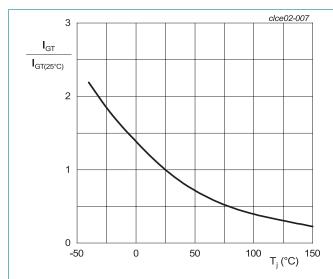


Fig. 7. Normalized gate trigger current as a function of junction temperature

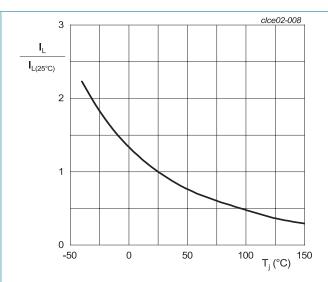


Fig. 8. Normalized latching current as a function of junction temperature

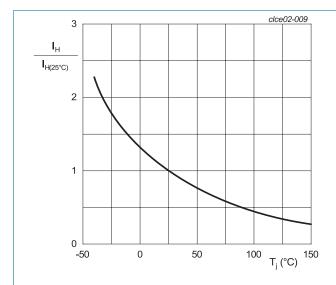
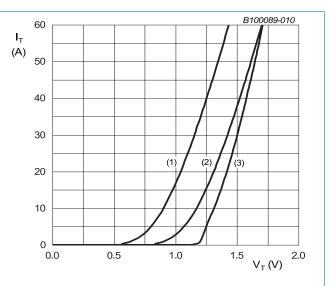


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 1.107 V; R_s = 0.0104 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

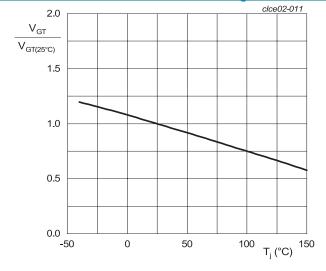
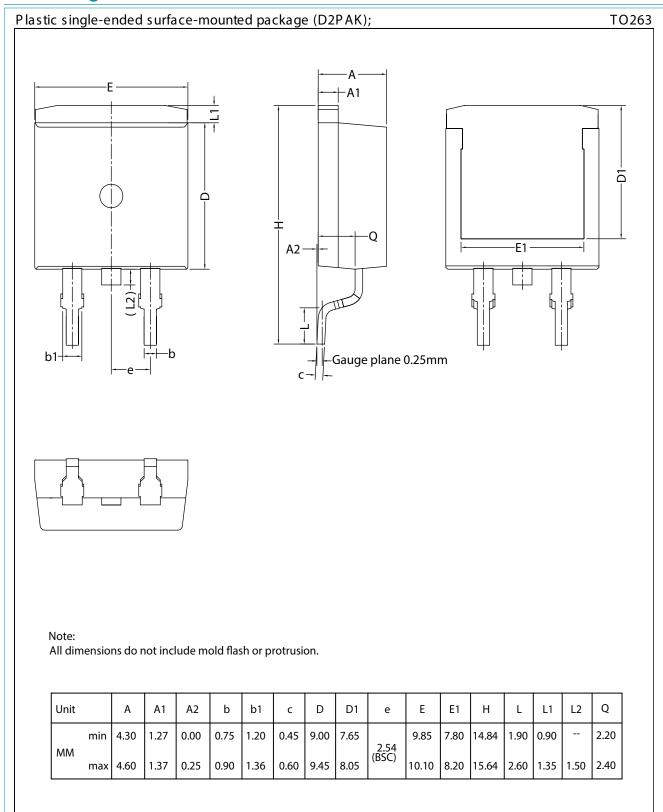


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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